

# Jir Pangrc

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

102  
papers

786  
citations

14  
h-index

20  
g-index

118  
ext. papers

857  
ext. citations

2.4  
avg, IF

3.33  
L-index

#	Paper	IF	Citations
102	Size and nitrogen inhomogeneity in detonation and laser synthesized primary nanodiamond particles revealed via salt-assisted deaggregation. <i>Carbon</i> , <b>2021</b> , 171, 230-239	10.4	7
101	Luminescence redshift of thick InGaN/GaN heterostructures induced by the migration of surface adsorbed atoms. <i>Journal of Crystal Growth</i> , <b>2021</b> , 565, 126151	1.6	1
100	Advancement toward ultra-thick and bright InGaN/GaN structures with a high number of QWs. <i>CrystEngComm</i> , <b>2019</b> , 21, 356-362	3.3	14
99	Influence of GaN buffer layer under InGaN/GaN MQWs on luminescent properties. <i>Journal of Crystal Growth</i> , <b>2019</b> , 507, 246-250	1.6	5
98	Strong suppression of In desorption from InGaN QW by improved technology of upper InGaN/GaN QW interface. <i>Journal of Crystal Growth</i> , <b>2019</b> , 507, 310-315	1.6	2
97	Influence of Si doping of GaN layers surrounding InGaN quantum wells on structure photoluminescence properties. <i>Journal of Crystal Growth</i> , <b>2019</b> , 506, 8-13	1.6	7
96	InGaN/GaN Structures: Effect of the Quantum Well Number on the Cathodoluminescent Properties. <i>Physica Status Solidi (B): Basic Research</i> , <b>2018</b> , 255, 1700464	1.3	4
95	Improvement of luminescence properties of GaN buffer layer for fast nitride scintillator structures. <i>Journal of Crystal Growth</i> , <b>2017</b> , 464, 221-225	1.6	10
94	GaAsSb-capped InAs QD type-II solar cell structures Improvement by composition profiling of layers surrounding QD. <i>Materials Research Express</i> , <b>2017</b> , 4, 025502	1.7	
93	InAs/GaSb/AlSb composite quantum well structure preparation with help of reflectance anisotropy spectroscopy. <i>Journal of Crystal Growth</i> , <b>2017</b> , 464, 206-210	1.6	4
92	Comparison of MOVPE grown GaAs, InGaAs and GaAsSb covering layers for different InAs/GaAs quantum dot applications. <i>Journal of Crystal Growth</i> , <b>2017</b> , 464, 59-63	1.6	5
91	Vertical transport in type-II heterojunctions with InAs/GaSb/AlSb composite quantum wells in a high magnetic field. <i>Semiconductors</i> , <b>2017</b> , 51, 1343-1349	0.7	1
90	Ultrathin Nanocrystalline Diamond Films with Silicon Vacancy Color Centers via Seeding by 2 nm Detonation Nanodiamonds. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 38842-38853	9.5	34
89	GaAsSb/InAs/(In)GaAs type II quantum dots for solar cell applications. <i>Journal of Crystal Growth</i> , <b>2017</b> , 464, 64-68	1.6	8
88	On the correlations between the excitonic luminescence efficiency and the QW numbers in multiple InGaN/GaN QW structure. <i>Journal of Applied Physics</i> , <b>2017</b> , 121, 214505	2.5	8
87	Growth and properties of the MOVPE GaAs/InAs/GaSb quantum dot structures. <i>Physica B: Condensed Matter</i> , <b>2016</b> , 480, 14-22	2.8	3
86	Microwave radiation absorption and Shubnikov-de Haas oscillations in semi-metal InAs/GaSb/AlSb composite quantum wells <b>2016</b> ,		1

85	Microwave radiation absorption by 2D-electrons in the type II composite InAs/GaSb/AlSb quantum wells in a magnetic field. <i>Journal of Physics: Conference Series</i> , <b>2016</b> , 769, 012075	0.3	
84	Microwave radiation absorption and Shubnikov-de Haas oscillations in semimetal InAs/GaSb/AlSb composite quantum wells. <i>Journal of Nanophotonics</i> , <b>2016</b> , 10, 046013	1.1	1
83	MOVPE prepared InAs/GaAs quantum dots covered by GaAsSb layer with long wavelength emission at 1.8 $\mu\text{m}$ . <i>Journal of Crystal Growth</i> , <b>2015</b> , 414, 167-171	1.6	8
82	Growth and properties of AlIIIbV QD structures for intermediate band solar cells. <i>Journal of Crystal Growth</i> , <b>2015</b> , 414, 172-176	1.6	9
81	Growth of InAs/GaAs quantum dots covered by GaAsSb in multiple structures studied by reflectance anisotropy spectroscopy. <i>Journal of Crystal Growth</i> , <b>2015</b> , 414, 156-160	1.6	14
80	Structural and photoluminescent properties of low temperature InAs buffer layer grown by MOVPE on GaAs substrates. <i>Journal of Crystal Growth</i> , <b>2014</b> , 396, 54-60	1.6	
79	Vapor Pressures of (3-(Dimethylamino)propyl)dimethylindium, (tert-Butylimino)bis(diethylamino)cyclopentadienyltantalum, and (tert-Butylimino)tris(ethylmethylamino)tantalum. <i>Journal of Chemical &amp; Engineering Data</i> , <b>2014</b> , 59, 4179-4183	2.8	
78	Misfit dislocation reduction in InGaAs epilayers grown on porous GaAs substrates. <i>Applied Surface Science</i> , <b>2014</b> , 306, 89-93	6.7	7
77	Two-band superlinear electroluminescence in GaSb based nanoheterostructures with AlSb/InAs $_{1-x}$ Sb $_x$ /AlSb deep quantum well. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 223102	2.5	2
76	Effect of the lower and upper interfaces on the quality of InAs/GaAs quantum dots. <i>Applied Surface Science</i> , <b>2014</b> , 301, 173-177	6.7	10
75	Epitaxial growth on porous GaAs substrates. <i>Comptes Rendus Chimie</i> , <b>2013</b> , 16, 59-64	2.7	9
74	Graded GaAsSb strain reducing layers covering InAs/GaAs quantum dots. <i>Journal of Crystal Growth</i> , <b>2013</b> , 370, 303-306	1.6	16
73	Photoelectric and luminescence properties of GaSb-Based nanoheterostructures with a deep Al(As)Sb/InAsSb/Al(As)Sb quantum well grown by metalorganic vapor-phase epitaxy. <i>Semiconductors</i> , <b>2013</b> , 47, 1041-1045	0.7	2
72	Type I/Type II band alignment of a GaAsSb/InAs/GaAs quantum dot heterostructure influenced by dot size and strain-reducing layer composition. <i>Journal Physics D: Applied Physics</i> , <b>2013</b> , 46, 095103	3	24
71	Light emitting diodes with InAs/GaAsSb self-assembled quantum dot layer embedded in GaAs. <i>Thin Solid Films</i> , <b>2013</b> , 543, 83-87	2.2	
70	Integral and local density of states of InAs quantum dots in GaAs/AlGaAs heterostructure observed by ballistic electron emission spectroscopy near one-electron ground state. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2013</b> , 48, 61-65	3	2
69	Vapor pressures of dimethylcadmium, trimethylbismuth, and tris(dimethylamino)antimony. <i>Fluid Phase Equilibria</i> , <b>2013</b> , 360, 106-110	2.5	4
68	Combined vertically correlated InAs and GaAsSb quantum dots separated by triangular GaAsSb barrier. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 174305	2.5	8

67	Superlinear electroluminescence due to impact ionization in GaSb-based heterostructures with deep Al(As)Sb/InAsSb/Al(As)Sb quantum wells. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 023108	2.5	10
66	Thermal conversion and epitaxial overgrowth of nanopores etched in InP and GaAs. <i>International Journal of Nanotechnology</i> , <b>2012</b> , 9, 732	1.5	1
65	Self-assembled InAs/GaAs quantum dots covered by different strain reducing layers exhibiting strong photo- and electroluminescence in 1.3 and 1.55 microm bands. <i>Journal of Nanoscience and Nanotechnology</i> , <b>2011</b> , 11, 6804-9	1.3	6
64	InAs/GaAs quantum dot capping in kinetically limited MOVPE growth regime. <i>Journal of Crystal Growth</i> , <b>2011</b> , 317, 39-42	1.6	1
63	Influence of strain reducing layers on electroluminescence and photoluminescence of InAs/GaAs QD structures. <i>Journal of Crystal Growth</i> , <b>2011</b> , 315, 110-113	1.6	11
62	Electro- and photoluminescence of InAs/GaAs quantum dot structures. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 245, 012080	0.3	
61	Vapor Pressure of Trimethylantimony and tert-Butyldimethylantimony. <i>Journal of Chemical &amp; Engineering Data</i> , <b>2010</b> , 55, 362-365	2.8	4
60	Vapor Pressure of Selected Organic Iodides. <i>Journal of Chemical &amp; Engineering Data</i> , <b>2010</b> , 55, 4780-4884	2.9	
59	Vapor Pressure of Tetrakis(dimethylamino)germanium. <i>Journal of Chemical &amp; Engineering Data</i> , <b>2010</b> , 55, 4095-4097	2.8	4
58	Quantum confinement in MOVPE-grown structures with self-assembled InAs/GaAs quantum dots. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 245, 012079	0.3	
57	Electroluminescence in p-InAs/AlSb/InAsSb/AlSb/p(n)-GaSb type II heterostructures with deep quantum wells at the interface. <i>Semiconductors</i> , <b>2010</b> , 44, 66-71	0.7	6
56	InGaAs and GaAsSb strain reducing layers covering InAs/GaAs quantum dots. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 1383-1387	1.6	16
55	Intense interface luminescence in type II narrow-gap InAs-based heterostructures at room temperature. <i>Physics Procedia</i> , <b>2010</b> , 3, 1189-1193		5
54	Surface processes during growth of InAs/GaAs quantum dot structures monitored by reflectance anisotropy spectroscopy. <i>Surface Science</i> , <b>2010</b> , 604, 318-321	1.8	22
53	InAs/GaAs quantum dot structures emitting in the 1.55 $\mu\text{m}$ band. <i>IOP Conference Series: Materials Science and Engineering</i> , <b>2009</b> , 6, 012007	0.4	1
52	Influence of capping layer thickness on electronic states in self assembled MOVPE grown InAs quantum dots in GaAs. <i>Superlattices and Microstructures</i> , <b>2009</b> , 46, 324-327	2.8	11
51	Preliminary comparison of ballistic electron emission spectroscopy measurements on InAs quantum dots in a GaAs/AlGaAs heterostructure grown by MBE and MOVPE. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 496-498	1.8	1
50	Ballistic electron emission spectroscopy/microscopy of self-assembled InAs quantum dots of different sizes embedded in GaAs/AlGaAs heterostructure. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 012101	3.4	5

49	Photovoltaic detector based on type II p-InAs/AlSb/InAsSb/AlSb/p-GaSb heterostructures with a single quantum well for mid-infrared spectral range <b>2008</b> ,		4
48	InAs/GaAs quantum dot structures covered by InGaAs strain reducing layer characterized by photomodulated reflectance. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2008</b> , 147, 175-178	3.1	7
47	Growth and properties of InAs/InxGa1-xAs/GaAs quantum dot structures. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 2229-2233	1.6	15
46	Vapor pressure of germanium precursors. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4720-4723	1.6	13
45	Influence of capping layer on the properties of MOVPE-grown InAs/GaAs quantum dots. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 5081-5084	1.6	6
44	Optical characterisation of MOVPE grown vertically correlated InAs/GaAs quantum dots. <i>Microelectronics Journal</i> , <b>2008</b> , 39, 1070-1074	1.8	14
43	Photoluminescence and magnetophotoluminescence of vertically stacked InAs/GaAs quantum dot structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2007</b> , 36, 106-113	3	12
42	Lateral shape of InAs/GaAs quantum dots in vertically correlated structures. <i>Journal of Crystal Growth</i> , <b>2007</b> , 298, 570-573	1.6	9
41	Properties of MOVPE InAs/GaAs quantum dots overgrown by InGaAs. <i>Journal of Crystal Growth</i> , <b>2007</b> , 298, 582-585	1.6	23
40	Study of InAs quantum dots in AlGaAs/GaAs heterostructure by ballistic electron emission microscopy/spectroscopy. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 042110	3.4	4
39	Transport-controlling deep defects in MOVPE grown GaSb. <i>Semiconductor Science and Technology</i> , <b>2006</b> , 21, 180-183	1.8	4
38	Room-temperature electroluminescence of AlSb/InAsSb single quantum wells grown by metal organic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 132102	3.4	5
37	1.3 μm emission from InAs/GaAs quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 3811-3814		8
36	Performance study of radiation detectors based on semi-insulating GaAs with P+ homo- and heterojunction blocking electrode. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2006</b> , 563, 159-162	1.2	2
35	Ultrathin InAs and modulated InGaAs layers in GaAs grown by MOVPE studied by photomodulated reflectance spectroscopy. <i>Applied Surface Science</i> , <b>2006</b> , 253, 85-89	6.7	2
34	Vapour pressure measurement of metal organic precursors used for MOVPE. <i>Journal of Chemical Thermodynamics</i> , <b>2006</b> , 38, 312-322	2.9	20
33	Vapor Pressure of Di-tert-butylsilane. <i>Journal of Chemical &amp; Engineering Data</i> , <b>2005</b> , 50, 1613-1615	2.8	11
32	GaSb based lasers operating near 2.3 microm for high resolution absorption spectroscopy. <i>Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy</i> , <b>2005</b> , 61, 3066-9	4.4	9

31	Room-temperature diode laser photoacoustic spectroscopy near 2.3 $\mu\text{m}$ . <i>Applied Physics B: Lasers and Optics</i> , <b>2005</b> , 81, 857-861	1.9	6
30	Optical characterization of MOVPE grown $\text{InAs}$ layers in GaAs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 1319-1324		
29	Electroluminescence of type II broken-gap p-Ga <sub>0.84</sub> In <sub>0.16</sub> As <sub>0.22</sub> Sb <sub>0.78</sub> $\beta$ -InAs heterostructures with a high-mobility electron channel at the interface. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 083512	2.5	1
28	Influence of growth rate on charge transport in GaSb homojunctions prepared by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 1811-1815	2.5	14
27	Vapour pressure and heat capacities of metal organic precursors, Y(thd) <sub>3</sub> and Zr(thd) <sub>4</sub> . <i>Journal of Crystal Growth</i> , <b>2004</b> , 264, 192-200	1.6	22
26	Measurement of vapour pressure of In-based metalorganics for MOVPE. <i>Journal of Crystal Growth</i> , <b>2004</b> , 272, 42-46	1.6	14
25	Influence of photon recycling on photovoltage spectra of GaSb diodes. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 5104-5110	2.5	1
24	InAs $\beta$ layer structures in GaAs grown by MOVPE and characterised by luminescence and photocurrent spectroscopy. <i>Journal of Crystal Growth</i> , <b>2003</b> , 248, 328-332	1.6	4
23	Vapor pressure of metal organic precursors. <i>Journal of Crystal Growth</i> , <b>2003</b> , 248, 99-107	1.6	30
22	Current-voltage characteristics of GaSb homojunctions prepared by MOVPE. <i>Solid-State Electronics</i> , <b>2003</b> , 47, 1471-1478	1.7	4
21	Charge transport study and spectral response of GaSb/GaAs heterojunctions prepared by MOVPE. <i>Solar Energy Materials and Solar Cells</i> , <b>2003</b> , 76, 135-145	6.4	4
20	Electroluminescence in a semimetal channel at a single type II broken-gap heterointerface. <i>Semiconductors</i> , <b>2003</b> , 37, 1185-1189	0.7	1
19	Magneto-photoluminescence study of electronic transitions in InAs/GaAs quantum dot layers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2002</b> , 88, 247-251	3.1	3
18	Lasers with $\text{InAs}$ layers in GaAs. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2002</b> , 88, 312-316	3.1	3
17	Polarization anisotropy of photoluminescence from multilayer InAs/GaAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 13, 229-232	3	8
16	Photovoltage spectroscopy of InAs/GaAs quantum dot structures. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 10103	2.5	20
15	Ga <sub>1-x</sub> In <sub>x</sub> Sb - MOVPE growth and thermodynamic model. <i>Semiconductor Science and Technology</i> , <b>2001</b> , 16, 759-762	1.8	2
14	Broken-gap heterojunction in the p-GaSb-n-InAs <sub>1-x</sub> Sb <sub>x</sub> (0.0.18) system. <i>Technical Physics Letters</i> , <b>2001</b> , 27, 964-966	0.7	10

13	InAs/GaAs multiple quantum dot structures grown by LP-MOVPE. <i>Thin Solid Films</i> , <b>2000</b> , 380, 101-104	2.2	6
12	InAs/GaAs lasers with very thin active layer. <i>Thin Solid Films</i> , <b>2000</b> , 380, 233-236	2.2	5
11	Strained In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs multiple quantum wells grown by MOVPE. <i>European Physical Journal D</i> , <b>1999</b> , 49, 805-811		
10	Electroluminescence and photoelectric properties of type II broken-gap n-In(Ga)As(Sb)/N-GaSb heterostructures. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 6264-6268	2.5	7
9	Study of InAs quantum dots in GaAs prepared on misoriented substrates. <i>Thin Solid Films</i> , <b>1998</b> , 336, 80-83	2.2	12
8	Simultaneous characterization of defect states in CVD diamond by PDS, EPR, Raman and photocurrent spectroscopies. <i>Diamond and Related Materials</i> , <b>1998</b> , 7, 1048-1053	3.5	10
7	Out-of-Plane Weak Localization in Two-Dimensional Electron Structures. <i>Physical Review Letters</i> , <b>1998</b> , 80, 4020-4023	7.4	7
6	Temperature behaviour of luminescence of free-standing porous silicon. <i>Solid State Communications</i> , <b>1994</b> , 89, 297-300	1.6	5
5	Origin of recombination transitions at the lattice-matched GaInAsSb-GaSb n-N type-II heterojunctions. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 4189-4193	2.5	3
4	On the transport mechanism in porous silicon. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 180-182	3.4	40
3	The luminescence behaviour of porous silicon layers. <i>Solid State Communications</i> , <b>1993</b> , 85, 347-350	1.6	10
2	Optical constants of electrochemically grown oxides on Ga-V semiconductor surfaces in the VUV region. <i>Physica Scripta</i> , <b>1990</b> , 41, 154-156	2.6	
1	Complexes of divalent platinum with diphenylphosphineacetic acid. <i>Collection of Czechoslovak Chemical Communications</i> , <b>1981</b> , 46, 1222-1228		3